CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT
SWITCHING DIODE
VOLTAGE 80 Volts CURRENT 25 mAmpere

CHN1NGP

APPLICATION
* Ultra high speed switching

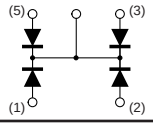
FEATURE
* Small surface mounting type. (SC-88A/SOT353)
* Multiple diodes in one small surface mount package.
* Suitable for high packing density.
* Maximum total power disspation is 150mW.
* Peak forward current is 80mA.

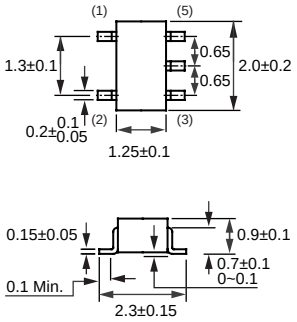
CONSTRUCTION
* Silicon epitaxial planar

MARKING
* DW

SC-88A/SOT353

CIRCUIT





Dimensions in millimeters

SC-88A/SOT353

MAXIMUM RATINGES (At T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	CHN1NGP	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	80	Volts
Maximum RMS Voltage	V_{RMS}	56	Volts
Maximum DC Blocking Voltage	V_{DC}	80	Volts
Maximum Average Forward Rectified Current	I_O	25	mAmps
Peak Forward Surge Current at 1uSec.	I_{FSM}	0.25	Amps
Typical Junction Capacitance between Terminal (Note 1)	C_J	3.5	pF
Maximum Reverse Recovery Time (Note 2)	T_{RR}	4.0	nSec
Maximum Operating Temperature Range	T_J	+150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (At T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	CHN1NGP	UNITS
Maximum Instantaneous Forward Voltage at I_F= 5mA	V_F	0.90	Volts
Maximum Average Reverse Current at V_R= 70V	I_R	0.1	uAmps

NOTES : 1. Measured at 1.0 MHz and applied reverse voltage of 6.0 volts.
2. Measured at applied froward current of 5mA and reverse voltage of 6.0 volts.
3. ESD sensitive product handling required.

2003-5

RATING CHARACTERISTIC CURVES (CHN1NGP)

FIG. 1 - POWER DERAING CURVE

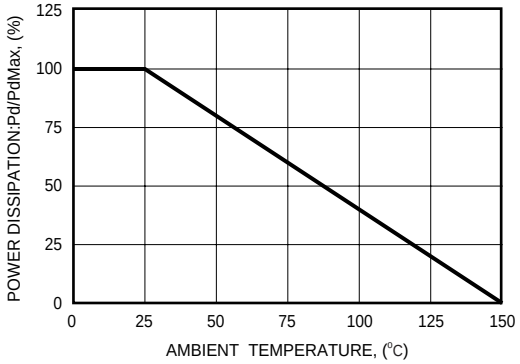


FIG. 2 - FORWARD CHARACTERISTICS

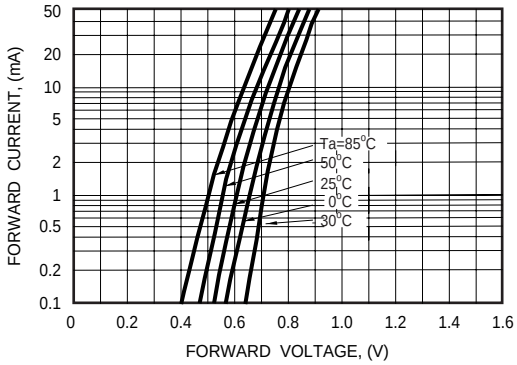


FIG. 3 - TYPICAL JUNCTION CAPACITANCE

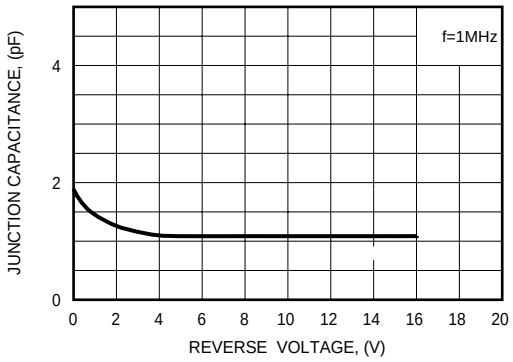


FIG. 4 - REVERSE CHARACTERISTICS

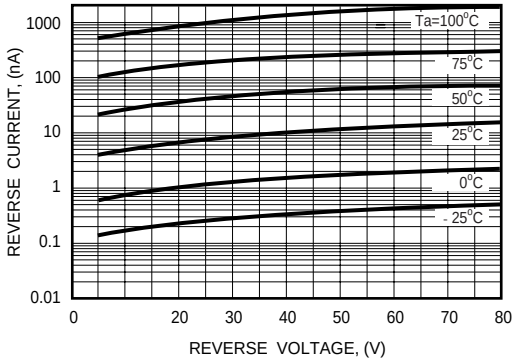


FIG. 5 - REVERSE RECOVERY TIME

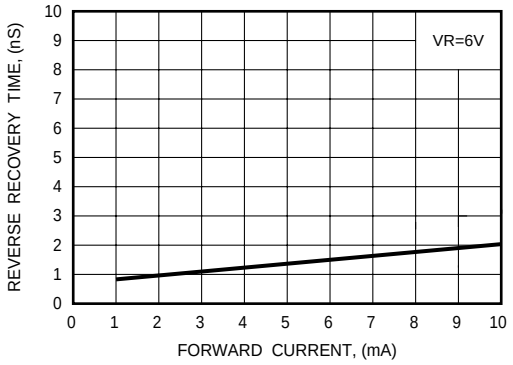


FIG. 6 - REVERSE RECOVERY TIME MEASUREMENT CIRCUIT